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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	149
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	96K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 29x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=spc5607bf1mlu6

1 Introduction

1.1 Document overview

This document describes the features of the family and options available within the family members, and highlights important electrical and physical characteristics of the device.

1.2 Description

This family of 32-bit system-on-chip (SoC) microcontrollers is the latest achievement in integrated automotive application controllers. It belongs to an expanding family of automotive-focused products designed to address the next wave of body electronics applications within the vehicle.

The advanced and cost-efficient e200z0h host processor core of this automotive controller family complies with the Power Architecture technology and only implements the VLE (variable-length encoding) APU (Auxiliary Processor Unit), providing improved code density. It operates at speeds of up to 64 MHz and offers high performance processing optimized for low power consumption. It capitalizes on the available development infrastructure of current Power Architecture devices and is supported with software drivers, operating systems and configuration code to assist with users implementations.

Table 1. MPC5607B family comparison[1]

Feature	MPC5605B			MPC5606B	MPC5607B
CPU	e200z0h				
Execution speed[2]	Up to 64 MHz				
Code flash memory	768 KB			1 MB	1.5 MB
Data flash memory	64 (4 × 16) KB				
SRAM	64 KB			80 KB	96 KB
MPU	8-entry				
eDMA	16 ch				
10-bit ADC	Yes				
dedicated[3]	7 ch	15 ch	29 ch	15 ch	29 ch
shared with 12-bit ADC	19 ch				
12-bit ADC	Yes				
dedicated[4]	5 ch				
shared with 10-bit ADC	19 ch				
Total timer I/O[5] eMIOS	37 ch, 16-bit	64 ch, 16-bit			
Counter / OPWM / ICOC[6]	10 ch				
O(I)PWM / OPWFMB / OPWMCB / ICOC[7]	7 ch				
O(I)PWM / ICOC[8]	7 ch	14 ch			
OPWM / ICOC[9]	13 ch	33 ch			
SCI (LINFlex)	4	8	10	8	10
SPI (DSPI)	3	5	6	5	6

3.3 Pad configuration during standby mode exit

Pad configuration (input buffer enable, pull enable) for low-power wakeup pads is controlled by both the SIUL and WKPU modules. During standby exit, all low power pads PA[0,1,2,4,15], PB[1,3,8,9,10][1], PC[7,9,11], PD[0,1], PE[0,9,11], PF[9,11,13][2], PG[3,5,7,9][2], PI[1,3][3] are configured according to their respective configuration done in the WKPU module. All other pads will have the same configuration as expected after a reset.

The TDO pad has been moved into the STANDBY domain in order to allow low-power debug handshaking in STANDBY mode. However, no pull-resistor is active on the TDO pad while in STANDBY mode. At this time the pad is configured as an input. When no debugger is connected the TDO pad is floating causing additional current consumption.

To avoid the extra consumption TDO must be connected. An external pull-up resistor in the range of 47–100 kOhms should be added between the TDO pin and VDD. Only if the TDO pin is used as an application pin and a pull-up cannot be used should a pull-down resistor with the same value be used instead between the TDO pin and GND.

3.4 Voltage supply pins

Voltage supply pins are used to provide power to the device. Three dedicated VDD_LV/VSS_LV supply pairs are used for 1.2 V regulator stabilization.

Table 3. Voltage supply pin descriptions

Port pin	Function	Pin number			
		100 LQFP	144 LQFP	176 LQFP	208 MAPBGA
VDD_HV	Digital supply voltage	15, 37, 70, 84	19, 51, 100, 123	6, 27, 59, 85, 124, 151	C2, D9, E16, G13, H3, N4, N9, R5
VSS_HV	Digital ground	14, 16, 35, 69, 83	18, 20, 49, 99, 122	7, 26, 28, 57, 86, 123, 150	G7, G8, G9, G10, H7, H8, H9, H10, J7, J8, J9, J10, K7, K8, K9, K10
VDD_LV	1.2 V decoupling pins. Decoupling capacitor must be connected between these pins and the nearest V_{SS_LV} pin.[1]	19, 32, 85	23, 46, 124	31, 54, 152	D8, K4, P7
VSS_LV	1.2 V decoupling pins. Decoupling capacitor must be connected between these pins and the nearest V_{DD_LV} pin.[1]	18, 33, 86	22, 47, 125	30, 55, 153	C8, J2, N7
VDD_BV	Internal regulator supply voltage	20	24	32	K3
VSS_HV_ADC0	Reference ground and analog ground for the A/D converter 0 (10-bit)	51	73	89	R15
VDD_HV_ADC0	Reference voltage and analog supply for the A/D converter 0 (10-bit)	52	74	90	P14
VSS_HV_ADC1	Reference ground and analog ground for the A/D converter 1 (12-bit)	59	81	98	N12

1. PB[8, 9] ports have wakeup functionality in all modes except STANDBY.
2. PF[9,11,13], PG[3,5,7,9], PI[1,3] are not available in the 100-pin LQFP.
3. PI[1,3] are not available in the 144-pin LQFP.

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								100 LQFP	144 LQFP	176 LQFP	208 MAP BGA[4]
PB[11]	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ADC0_S[3]	SIUL eMIOS_0 — DSPI_0 ADC_0	I/O I/O — I/O I	J	Tristate	—	—	97	N13
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ADC0_X[0]	SIUL eMIOS_0 — DSPI_0 ADC_0	I/O I/O — O I	J	Tristate	61	83	101	M16
PB[13]	PCR[29]	AF0 AF1 AF2 AF3 —	GPIO[29] E0UC[5] — CS2_0 ADC0_X[1]	SIUL eMIOS_0 — DSPI_0 ADC_0	I/O I/O — O I	J	Tristate	63	85	103	M13
PB[14]	PCR[30]	AF0 AF1 AF2 AF3 —	GPIO[30] E0UC[6] — CS3_0 ADC0_X[2]	SIUL eMIOS_0 — DSPI_0 ADC_0	I/O I/O — O I	J	Tristate	65	87	105	L16
PB[15]	PCR[31]	AF0 AF1 AF2 AF3 —	GPIO[31] E0UC[7] — CS4_0 ADC0_X[3]	SIUL eMIOS_0 — DSPI_0 ADC_0	I/O I/O — O I	J	Tristate	67	89	107	L13
Port C											
PC[0][10]	PCR[32]	AF0 AF1 AF2 AF3	GPIO[32] — TDI —	SIUL — JTAGC —	I/O — I —	M	Input, weak pull-up	87	126	154	A8
PC[1][10]	PCR[33]	AF0 AF1 AF2 AF3	GPIO[33] — TDO —	SIUL — JTAGC —	I/O — O —	F[11]	Tristate	82	121	149	C9
PC[2]	PCR[34]	AF0 AF1 AF2 AF3 —	GPIO[34] SCK_1 CAN4TX DEBUG[0] EIRQ[5]	SIUL DSPI_1 FlexCAN_4 SSCM SIUL	I/O I/O O O I	M	Tristate	78	117	145	A11

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								100 LQFP	144 LQFP	176 LQFP	208 MAP BGA[4]
PC[11]	PCR[43]	AF0 AF1 AF2 AF3 — — —	GPIO[43] — — MA[2] WKPU[5][5] CAN1RX CAN4RX	SIUL — — ADC_0 WKPU FlexCAN_1 FlexCAN_4	I/O — — O I I I	S	Tristate	21	27	35	M4
PC[12]	PCR[44]	AF0 AF1 AF2 AF3 — —	GPIO[44] E0UC[12] — — EIRQ[19] SIN_2	SIUL eMIOS_0 — — SIUL DSPI_2	I/O I/O — — I I	M	Tristate	97	141	173	B4
PC[13]	PCR[45]	AF0 AF1 AF2 AF3	GPIO[45] E0UC[13] SOUT_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O O —	S	Tristate	98	142	174	A2
PC[14]	PCR[46]	AF0 AF1 AF2 AF3 —	GPIO[46] E0UC[14] SCK_2 — EIRQ[8]	SIUL eMIOS_0 DSPI_2 — SIUL	I/O I/O I/O — I	S	Tristate	3	3	3	C1
PC[15]	PCR[47]	AF0 AF1 AF2 AF3 —	GPIO[47] E0UC[15] CS0_2 — EIRQ[20]	SIUL eMIOS_0 DSPI_2 — SIUL	I/O I/O I/O — I	M	Tristate	4	4	4	D3
Port D											
PD[0]	PCR[48]	AF0 AF1 AF2 AF3 — — —	GPIO[48] — — — WKPU[27][5] ADC0_P[4] ADC1_P[4]	SIUL — — — WKPU ADC_0 ADC_1	I — — — I I I	I	Tristate	41	63	77	P12
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 — — —	GPIO[49] — — — WKPU[28][5] ADC0_P[5] ADC1_P[5]	SIUL — — — WKPU ADC_0 ADC_1	I — — — I I I	I	Tristate	42	64	78	T12

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET configuration[3]	Pin number			
								100 LQFP	144 LQFP	176 LQFP	208 MAP BGA[4]
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 — —	GPIO[50] — — — ADC0_P[6] ADC1_P[6]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	43	65	79	R12
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 — —	GPIO[51] — — — ADC0_P[7] ADC1_P[7]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	44	66	80	P13
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 — —	GPIO[52] — — — ADC0_P[8] ADC1_P[8]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	45	67	81	R13
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 — —	GPIO[53] — — — ADC0_P[9] ADC1_P[9]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	46	68	82	T13
PD[6]	PCR[54]	AF0 AF1 AF2 AF3 — —	GPIO[54] — — — ADC0_P[10] ADC1_P[10]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	47	69	83	T14
PD[7]	PCR[55]	AF0 AF1 AF2 AF3 — —	GPIO[55] — — — ADC0_P[11] ADC1_P[11]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	48	70	84	R14
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPIO[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	49	71	87	T15

[1] Alternate functions are chosen by setting the values of the PCR.PA bitfields inside the SIUL module. PCR.PA = 00 → AF0; PCR.PA = 01 → AF1; PCR.PA = 10 → AF2; PCR.PA = 11 → AF2. This is intended to select the output functions; to use one of the input functions, the PCR.IBE bit must be written to '1', regardless of the values selected in the PCR.PA bitfields. For this reason, the value corresponding to an input only function is reported as "—".

[2] Multiple inputs are routed to all respective modules internally. The input of some modules must be configured by setting the values of the PSMIO.PADSELx bitfields inside the SIUL module.

[3] The RESET configuration applies during and after reset.

[4] **208 MAPBGA available only as development package for Nexus2+**

[5] All WKPU pins also support external interrupt capability. See the WKPU chapter for further details.

[6] NMI has higher priority than alternate function. When NMI is selected, the PCR.AF field is ignored.

[7] "Not applicable" because these functions are available only while the device is booting. Refer to the BAM information for details.

[8] Value of PCR.IBE bit must be 0

[9] This wakeup input cannot be used to exit STANDBY mode.

[10] Out of reset all the functional pins except PC[0:1] and PH[9:10] are available to the user as GPIO.
PC[0:1] are available as JTAG pins (TDI and TDO respectively).
PH[9:10] are available as JTAG pins (TCK and TMS respectively).
It is up to the user to configure these pins as GPIO when needed.

[11] PC[1] is a fast/medium pad but is in medium configuration by default. This pad is in Alternate Function 2 mode after reset which has TDO functionality. The reset value of PCR.OBE is '1', but this setting has no impact as long as this pad stays in AF2 mode. After configuring this pad as GPIO (PCR.PA = 0), output buffer is enabled as reset value of PCR.OBE = 1.

[12] Not available in 100 LQFP package

3.8 Nexus 2+ pins

In the 208 MAPBGA package, eight additional debug pins are available (see Table 6).

Table 6. Nexus 2+ pin descriptions

Port pin	Function	I/O direction	Pad type	Function after reset	Pin number		
					100 LQFP	144 LQFP	208 MAP BGA[1]
MCKO	Message clock out	O	F	—	—	—	T4
MDO0	Message data out 0	O	M	—	—	—	H15
MDO1	Message data out 1	O	M	—	—	—	H16
MDO2	Message data out 2	O	M	—	—	—	H14
MDO3	Message data out 3	O	M	—	—	—	H13
$\overline{\text{EVTI}}$	Event in	I	M	Pull-up	—	—	K1
$\overline{\text{EVTO}}$	Event out	O	M	—	—	—	L4
$\overline{\text{MSEO}}$	Message start/end out	O	M	—	—	—	G16

[1] **208 MAPBGA available only as development package for Nexus2+**

Table 12. Recommended operating conditions (3.3 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC0, VSS_HV_ADC1 (ADC reference) pin with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V
V_{DD_ADC}[4]	SR	Voltage on VDD_HV_ADC0, VDD_HV_ADC1 (ADC reference) with respect to ground (V_{SS})	—	3.0[5]	3.6	V
			Relative to V_{DD}	V_{DD} – 0.1	V_{DD} + 0.1	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	V_{SS} – 0.1	—	V
			Relative to V_{DD}	—	V_{DD} + 0.1	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
TV_{DD}	SR	V_{DD} slope to ensure correct power up[6]	—	—	0.25	V/µs
$T_{A\ C\text{-}Grade\ Part}$	SR	Ambient temperature under bias	f_{CPU} < 64 MHz[7]	–40	85	°C
$T_{J\ C\text{-}Grade\ Part}$	SR	Junction temperature under bias	—	–40	110	
$T_{A\ V\text{-}Grade\ Part}$	SR	Ambient temperature under bias	f_{CPU} < 64 MHz[7]	–40	105	
$T_{J\ V\text{-}Grade\ Part}$	SR	Junction temperature under bias	—	–40	130	
$T_{A\ M\text{-}Grade\ Part}$	SR	Ambient temperature under bias	f_{CPU} < 64 MHz[7]	–40	125	
$T_{J\ M\text{-}Grade\ Part}$	SR	Junction temperature under bias	—	–40	150	

1 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.

2 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.

3 470 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics). Supply ramp slope on VDD_BV should always be faster or equal to slope of VDD_HV. Otherwise, device may enter regulator bypass mode if slope on VDD_BV is slower.

4 100 nF capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair.

5 Full electrical specification cannot be guaranteed when voltage drops below 3.0 V. In particular, ADC electrical characteristics and I/Os DC electrical specification may not be guaranteed. When voltage drops below V_{LVDHVL}, device is reset.

6 Guaranteed by device validation

7 This frequency includes the 4% frequency modulation guardband.

Table 13. Recommended operating conditions (5.0 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	SR	Digital ground on VSS_HV pins	—	0	0	V
V_{DD}[1]	SR	Voltage on VDD_HV pins with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop[2]	3.0	5.5	
V_{SS_LV}[3]	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V_{SS})	—	V_{SS} – 0.1	V_{SS} + 0.1	V

4.5 Thermal characteristics

4.5.1 External ballast resistor recommendations

External ballast resistor on V_{DD_BV} pin helps in reducing the overall power dissipation inside the device. This resistor is required only when maximum power consumption exceeds the limit imposed by package thermal characteristics.

As stated in Table 14 LQFP thermal characteristics, considering a thermal resistance of 144 LQFP as 48.3 °C/W, at ambient temperature T_A = 125 °C, the junction temperature T_j will cross 150 °C if the total power dissipation is greater than (150 – 125)/48.3 = 517 mW. Therefore, the total device current I_{DDMAX} at 125 °C/5.5 V must not exceed 94.1 mA (i.e., PD/VDD). Assuming an average $I_{DD}(V_{DD\_HV})$ of 15–20 mA consumption typically during device RUN mode, the LV domain consumption $I_{DD}(V_{DD\_BV})$ is thus limited to $I_{DDMAX} - I_{DD}(V_{DD\_HV})$, i.e., 80 mA.

Therefore, respecting the maximum power allowed as explained in Section 4.5.2, “Package thermal characteristics, it is recommended to use this resistor only in the 125 °C/5.5 V operating corner as per the following guidelines:

- If $I_{DD}(V_{DD\_BV}) < 80$ mA, then no resistor is required.
- If 80 mA < $I_{DD}(V_{DD\_BV}) < 90$ mA, then 4 Ω resistor can be used.
- If $I_{DD}(V_{DD\_BV}) > 90$ mA, then 8 Ω resistor can be used.

Using resistance in the range of 4–8 Ω, the gain will be around 10–20% of total consumption on V_{DD_BV}. For example, if 8 Ω resistor is used, then power consumption when $I_{DD}(V_{DD\_BV})$ is 110 mA is equivalent to power consumption when $I_{DD}(V_{DD\_BV})$ is 90 mA (approximately) when resistor not used.

In order to ensure correct power up, the minimum V_{DD_BV} to be guaranteed is 30 ms/V. If the supply ramp is slower than this value, then LVDHV3B monitoring ballast supply V_{DD_BV} pin gets triggered leading to device reset. Until the supply reaches certain threshold, this low voltage detector (LVD) generates destructive reset event in the system. This threshold depends on the maximum $I_{DD}(V_{DD\_BV})$ possible across the external resistor.

4.5.2 Package thermal characteristics

Table 14. LQFP thermal characteristics[1]

Symbol		C	Parameter	Conditions[2]	Pin count	Value			Unit
						Min	Typ	Max	
$R_{\theta JA}$	CC	D	Thermal resistance, junction-to-ambient natural convection[3]	Single-layer board — 1s	100	—	—	64	°C/W
					144	—	—	64	
					176	—	—	64	
				Four-layer board — 2s2p	100	—	—	49.7	
					144	—	—	48.3	
					176	—	—	47.3	
$R_{\theta JB}$	CC		Thermal resistance, junction-to-board[4]	Single-layer board — 1s	100	—	—	36	°C/W
					144	—	—	38	
					176	—	—	38	
				Four-layer board — 2s2p	100	—	—	33.6	
					144	—	—	33.4	
					176	—	—	33.4	

Table 17. SLOW configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
V_{OH}	CC	P	Output high level SLOW configuration	Push Pull	I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	$0.8V_{DD}$	—	—	V
		C			I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	$0.8V_{DD}$	—	—	
		C			I_{OH} = –1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V_{DD} – 0.8	—	—	
V_{OL}	CC	P	Output low level SLOW configuration	Push Pull	I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
		C			I_{OL} = 2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	—	—	$0.1V_{DD}$	
		C			I_{OL} = 1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

[2] The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 18. MEDIUM configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
V_{OH}	CC	C	Output high level MEDIUM configuration	Push Pull	I_{OH} = –3.8 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	$0.8V_{DD}$	—	—	V
		P			I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	$0.8V_{DD}$	—	—	
		C			I_{OH} = –1 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[2]	$0.8V_{DD}$	—	—	
		C			I_{OH} = –1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V_{DD} – 0.8	—	—	
		C			I_{OH} = –100 µA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	$0.8V_{DD}$	—	—	

[2] The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

4.6.4 Output pin transition times

Table 20. Output pin transition times

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
T_{tr}	CC	D	Output transition time output pin[2] SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	50	ns
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
T_{tr}	CC	D	Output transition time output pin[2] MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	10	ns
		T		C_L = 50 pF		—	—	20	
		D		C_L = 100 pF		—	—	40	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	12	
		T		C_L = 50 pF		—	—	25	
		D		C_L = 100 pF		—	—	40	
T_{tr}	CC	D	Output transition time output pin[2] FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	4	ns
				C_L = 50 pF		—	—	6	
				C_L = 100 pF		—	—	12	
				C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	4	
				C_L = 50 pF		—	—	7	
				C_L = 100 pF		—	—	12	

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

[2] C_L includes device and package capacitances (C_{PKG} < 5 pF).

4.6.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in Table 21.

Table 22 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 23. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
1	—	—	PH[15]	2%	3%	3%	3%	—	—	—	—
	—	—	PH[13]	3%	4%	3%	4%	—	—	—	—
	—	—	PH[14]	3%	4%	4%	4%	—	—	—	—
	—	—	PI[6]	4%	—	4%	—	—	—	—	—
	—	—	PI[7]	4%	—	4%	—	—	—	—	—
	4	—	PG[5]	4%	—	5%	—	10%	—	12%	—
		—	PG[4]	4%	6%	5%	5%	9%	13%	11%	12%
		—	PG[3]	4%	—	5%	—	9%	—	11%	—
		—	PG[2]	4%	6%	5%	5%	9%	12%	10%	11%
		4	PA[2]	4%	—	5%	—	8%	—	10%	—
			PE[0]	4%	—	5%	—	8%	—	9%	—
			PA[1]	4%	—	5%	—	8%	—	9%	—
			PE[1]	4%	6%	5%	6%	7%	10%	9%	9%
			PE[8]	4%	6%	5%	6%	7%	10%	8%	9%
			PE[9]	4%	—	5%	—	6%	—	8%	—
			PE[10]	4%	—	5%	—	6%	—	7%	—
			PA[0]	4%	6%	5%	5%	6%	8%	7%	7%
			PE[11]	4%	—	5%	—	5%	—	6%	—

4.7 $\overline{\text{RESET}}$ electrical characteristics

The device implements a dedicated bidirectional $\overline{\text{RESET}}$ pin.

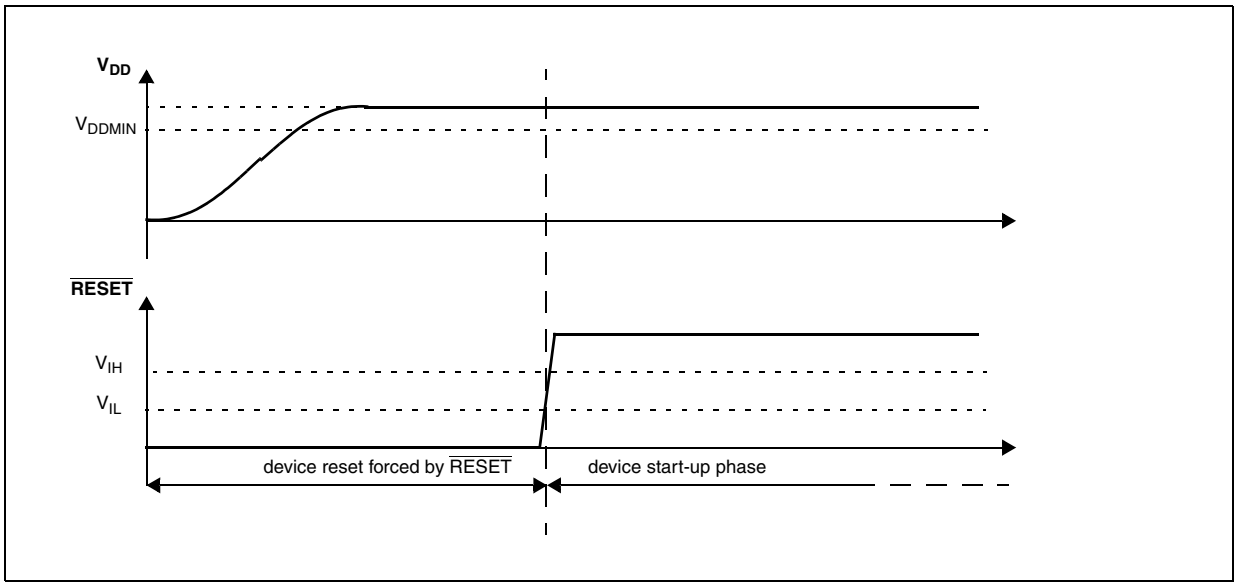


Figure 7. Start-up reset requirements

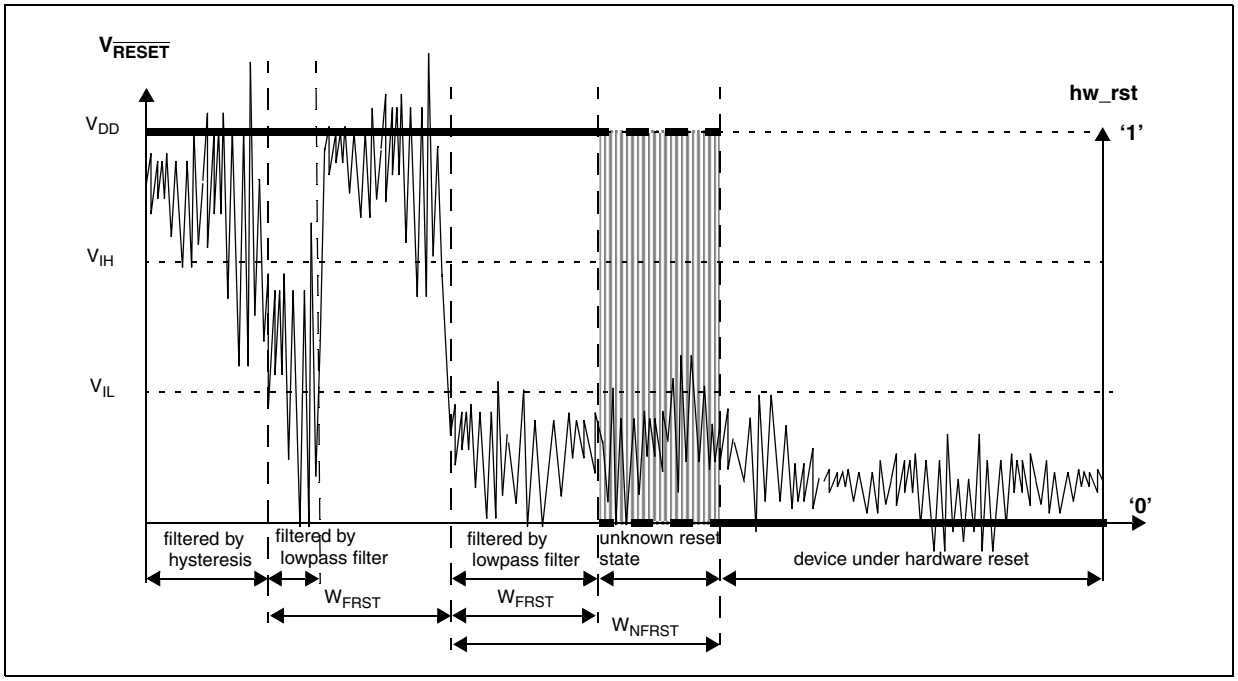


Figure 8. Noise filtering on reset signal

Table 34. ESD absolute maximum ratings[1,2]

Symbol	Ratings	Conditions	Class	Max value[3]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)	T_A = 25 °C conforming to AEC-Q100-003	M2	200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500	
				750 (corners)	

1 All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

2 A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

3 Data based on characterization results, not tested in production

4.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

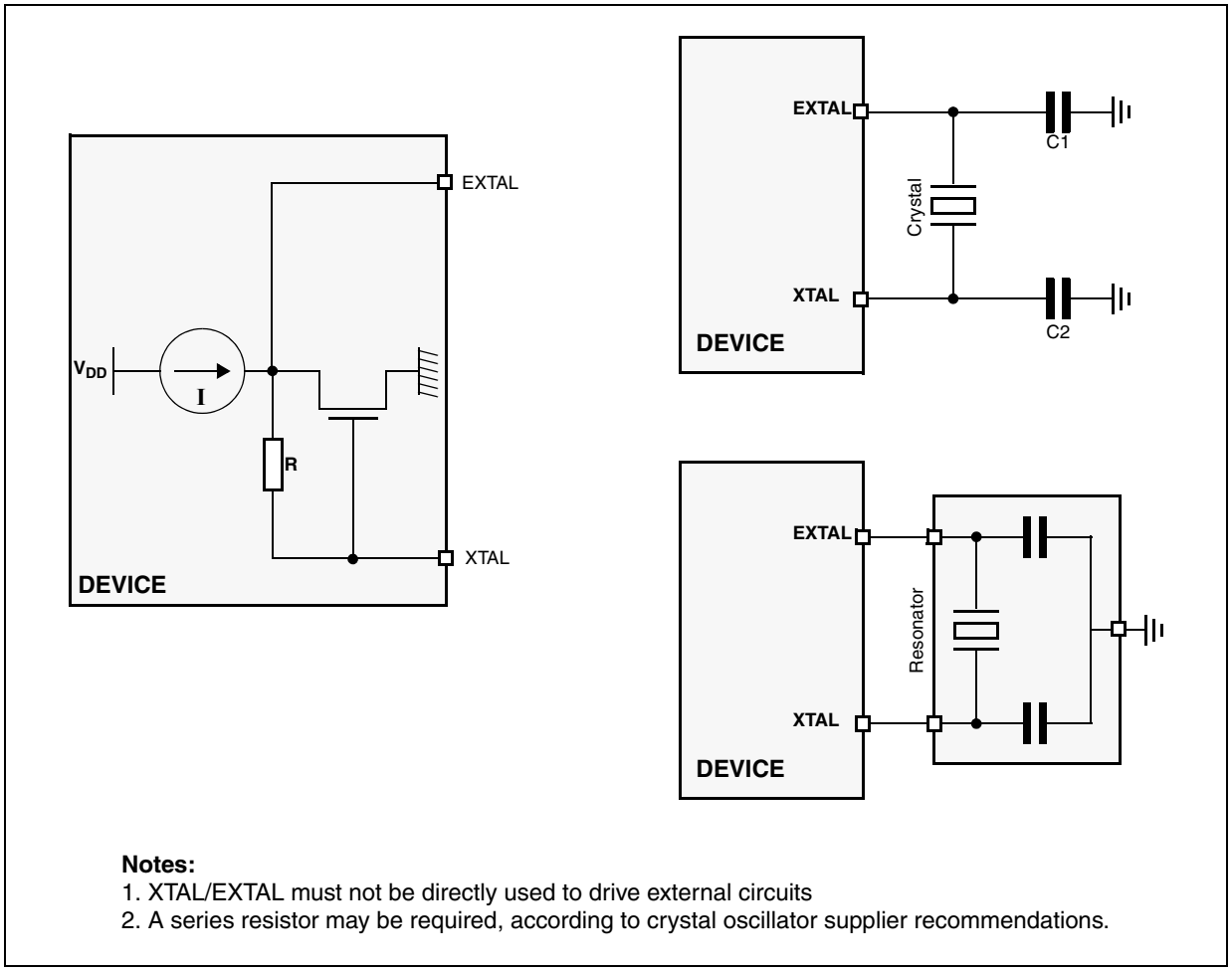
Table 35. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = 125 °C conforming to JESD 78	II level A

4.12 Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

The device provides an oscillator/resonator driver. Figure 11 describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Table 36 provides the parameter description of 4 MHz to 16 MHz crystals used for the design simulations.



Notes:
1. XTAL/EXTAL must not be directly used to drive external circuits
2. A series resistor may be required, according to crystal oscillator supplier recommendations.

Figure 11. Crystal oscillator and resonator connection scheme

Table 36. Crystal description

Nominal frequency (MHz)	NDK crystal reference	Crystal equivalent series resistance ESR Ω	Crystal motional capacitance (C_m) fF	Crystal motional inductance (L_m) mH	Load on xtalin/xtalout C1 = C2 (pF)[1]	Shunt capacitance between xtalout and xtalin C0[2] (pF)
4	NX8045GB	300	2.68	591.0	21	2.93
8	NX5032GA	300	2.46	160.7	17	3.01
10		150	2.93	86.6	15	2.91
12		120	3.11	56.5	15	2.93
16		120	3.90	25.3	10	3.00

1 The values specified for C1 and C2 are the same as used in simulations. It should be ensured that the testing includes all the parasitics (from the board, probe, crystal, etc.) as the AC / transient behavior depends upon them.

2 The value of C0 specified here includes 2 pF additional capacitance for parasitics (to be seen with bond-pads, package, etc.).

Table 41. Fast internal RC oscillator (16 MHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
$I_{FIRCSTOP}$	CC	T	Fast internal RC oscillator high frequency and system clock current in stop mode	T_A = 25 °C	sysclk = off	—	500	—	µA
					sysclk = 2 MHz	—	600	—	
					sysclk = 4 MHz	—	700	—	
					sysclk = 8 MHz	—	900	—	
					sysclk = 16 MHz	—	1250	—	
t_{FIRCSU}	CC	C	Fast internal RC oscillator start-up time	V_{DD} = 5.0 V ± 10%		—	1.1	2.0	µs
$\Delta_{FIRCPRE}$	CC	C	Fast internal RC oscillator precision after software trimming of f_{FIRC}	T_A = 25 °C		–1	—	1	%
$\Delta_{FIRCTRIM}$	CC	C	Fast internal RC oscillator trimming step	T_A = 25 °C		—	1.6		%
$\Delta_{FIRCVAR}$	CC	C	Fast internal RC oscillator variation over temperature and supply with respect to f_{FIRC} at T_A = 25 °C in high-frequency configuration	—		–5	—	5	%

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 This does not include consumption linked to clock tree toggling and peripherals consumption when RC oscillator is ON.

4.16 Slow internal RC oscillator (128 kHz) electrical characteristics

The device provides a 128 kHz low power internal RC oscillator. This can be used as the reference clock for the RTC module.

Table 42. Slow internal RC oscillator (128 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
f_{SIRC}	CC	P	Slow internal RC oscillator low frequency	T_A = 25 °C, trimmed	—	128	—	kHz
	SR	—		—	100	—	150	
I_{SIRC}[2],	CC	C	Slow internal RC oscillator low frequency current	T_A = 25 °C, trimmed	—	—	5	µA
t_{SIRCSU}	CC	P	Slow internal RC oscillator start-up time	T_A = 25 °C, V_{DD} = 5.0 V ± 10%	—	8	12	µs
$\Delta_{SIRCPRE}$	CC	C	Slow internal RC oscillator precision after software trimming of f_{SIRC}	T_A = 25 °C	–2	—	2	%
$\Delta_{SIRCTRIM}$	CC	C	Slow internal RC oscillator trimming step	—	—	2.7	—	

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: C_S being substantially a switched capacitance, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S equal to 3 pF, a resistance of 330 kΩ is obtained (R_{EQ} = 1 / (fc*C_S), where fc represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S) and the sum of $R_S + R_F + R_L + R_{SW} + R_{AD}$, the external circuit must be designed to respect the Equation 4:

Eqn. 4

$$V_A \bullet \frac{R_S + R_F + R_L + R_{SW} + R_{AD}}{R_{EQ}} < \frac{1}{2} LSB$$

Equation 4 generates a constraint for external network design, in particular on resistive path. Internal switch resistances (R_{SW} and R_{AD}) can be neglected with respect to external resistances.

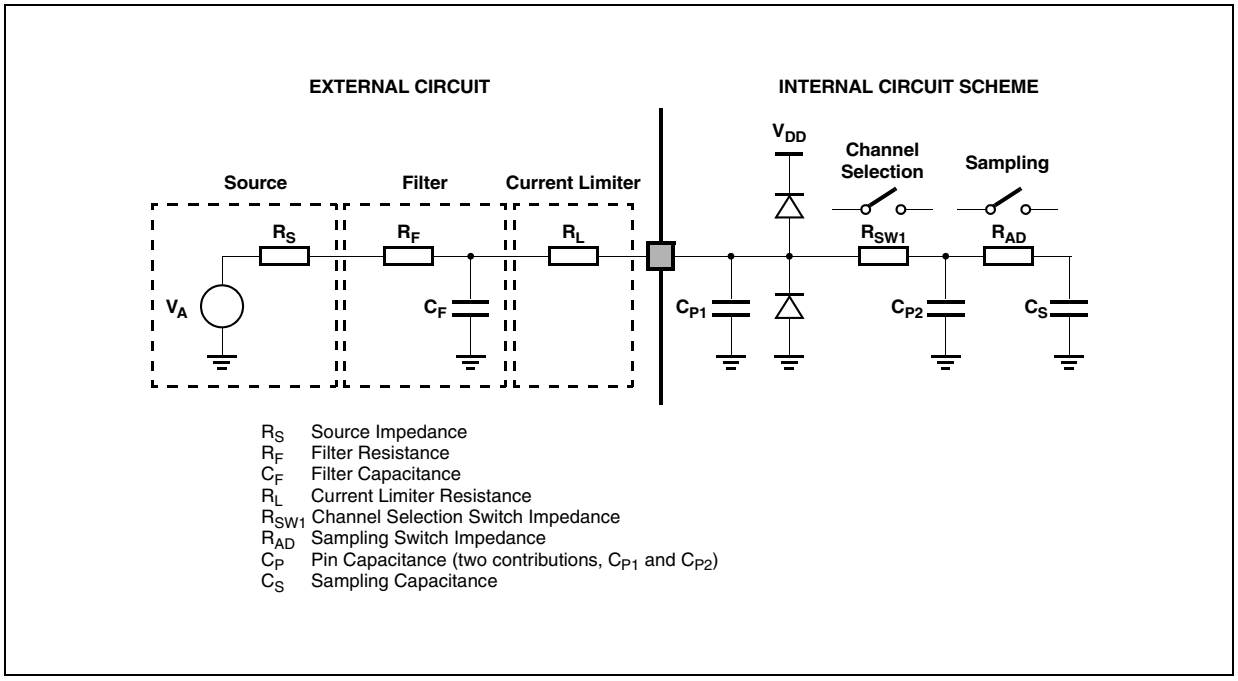


Figure 17. Input equivalent circuit (precise channels)

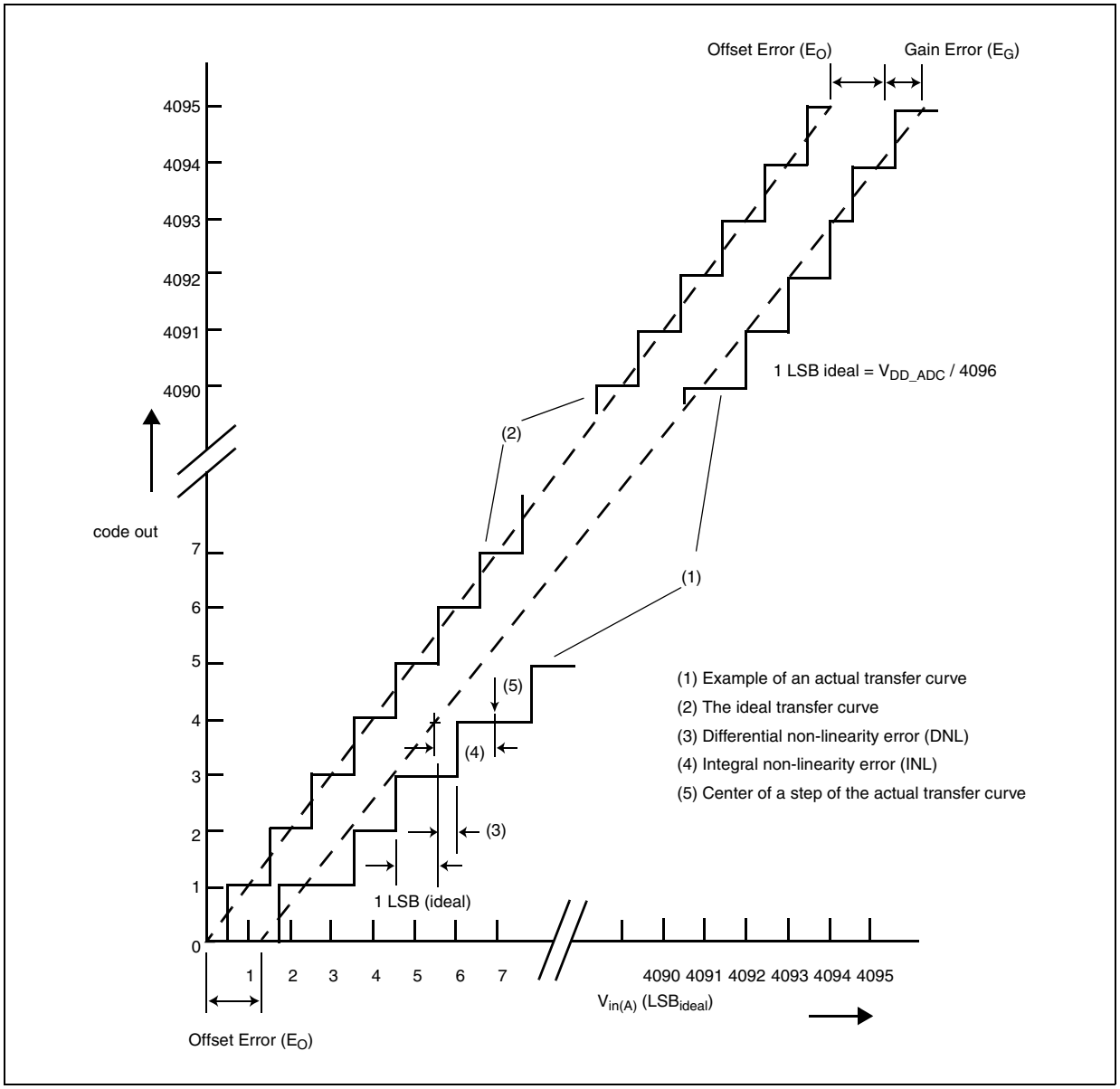


Figure 21. ADC_1 characteristic and error definitions

Table 45. ADC_1 conversion characteristics (12-bit ADC_1)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{SS_ADC1}	SR	—	Voltage on VSS_HV_ADC1 (ADC_1 reference) pin with respect to ground (V_{SS})[2]	—	–0.1	—	0.1	V
V_{DD_ADC1}	SR	—	Voltage on VDD_HV_ADC1 pin (ADC_1 reference) with respect to ground (V_{SS})	—	V_{DD} – 0.1	—	V_{DD} + 0.1	V

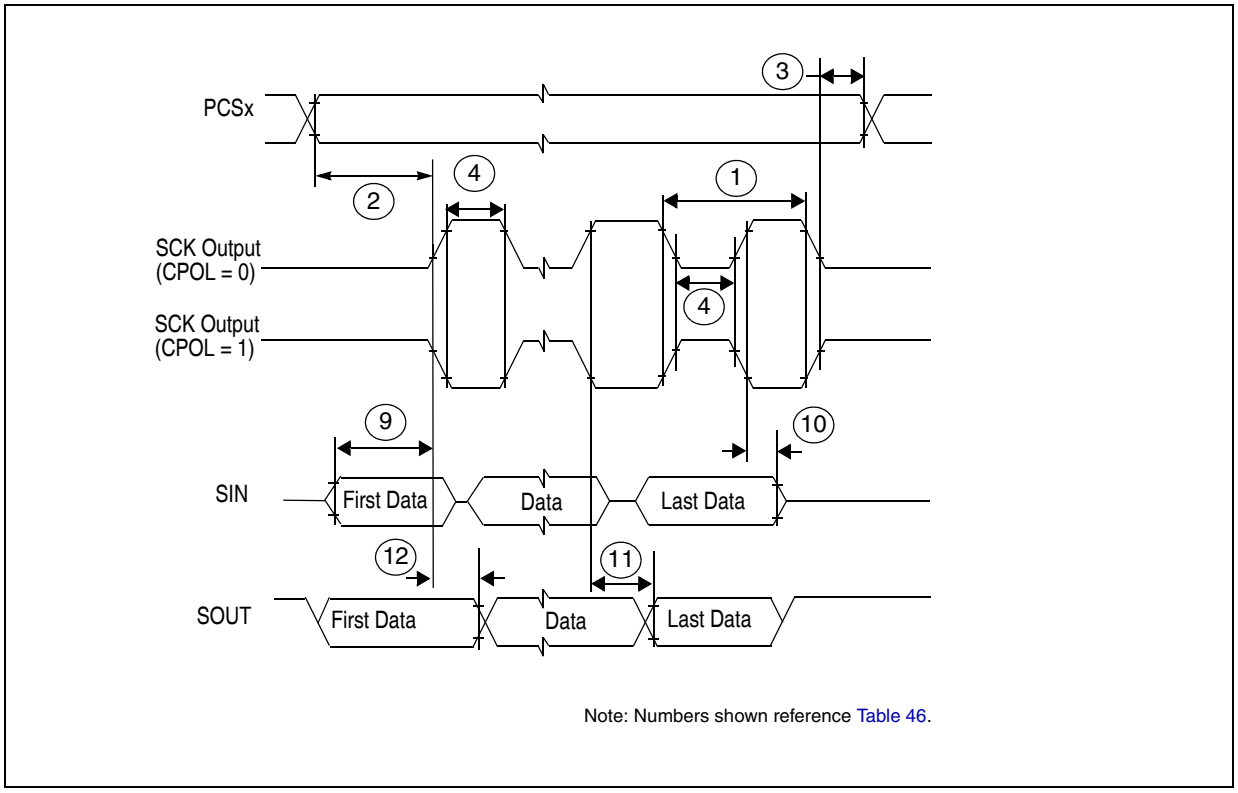


Figure 26. DSPI modified transfer format timing — master, CPHA = 0

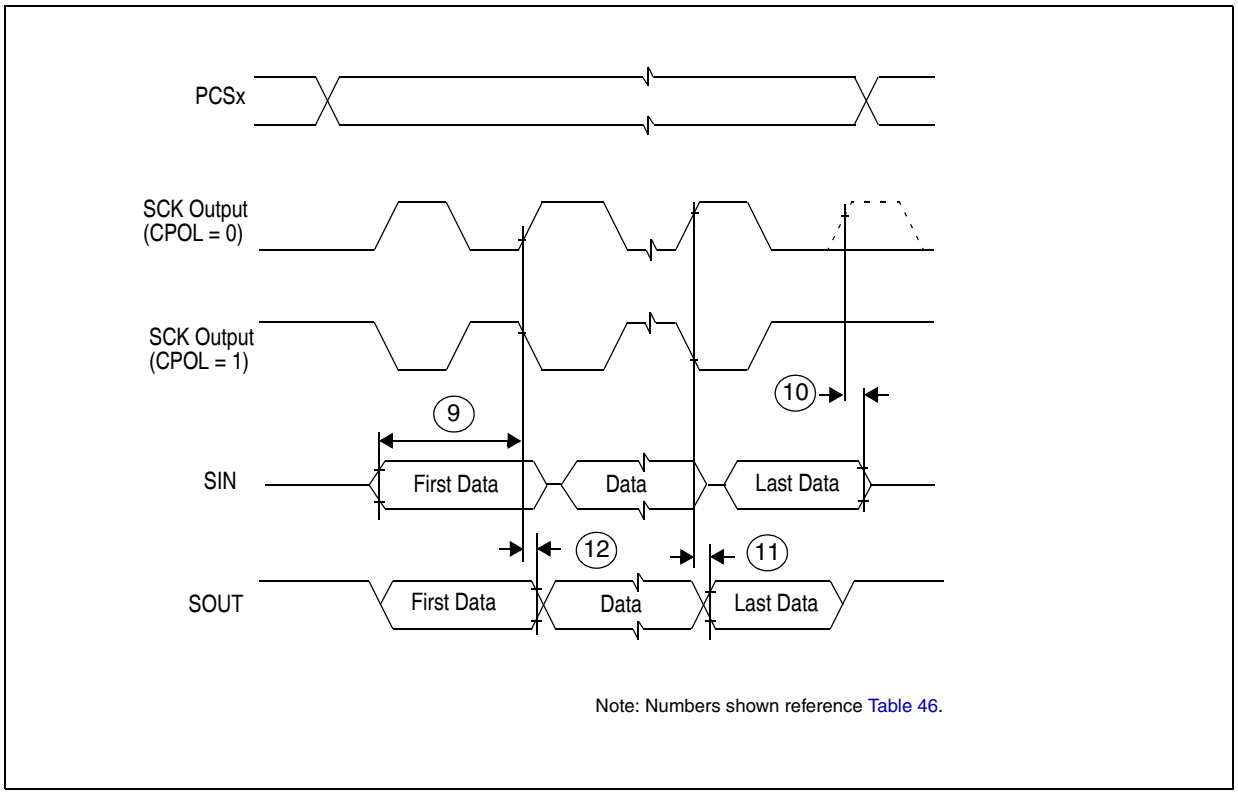


Figure 27. DSPI modified transfer format timing — master, CPHA = 1

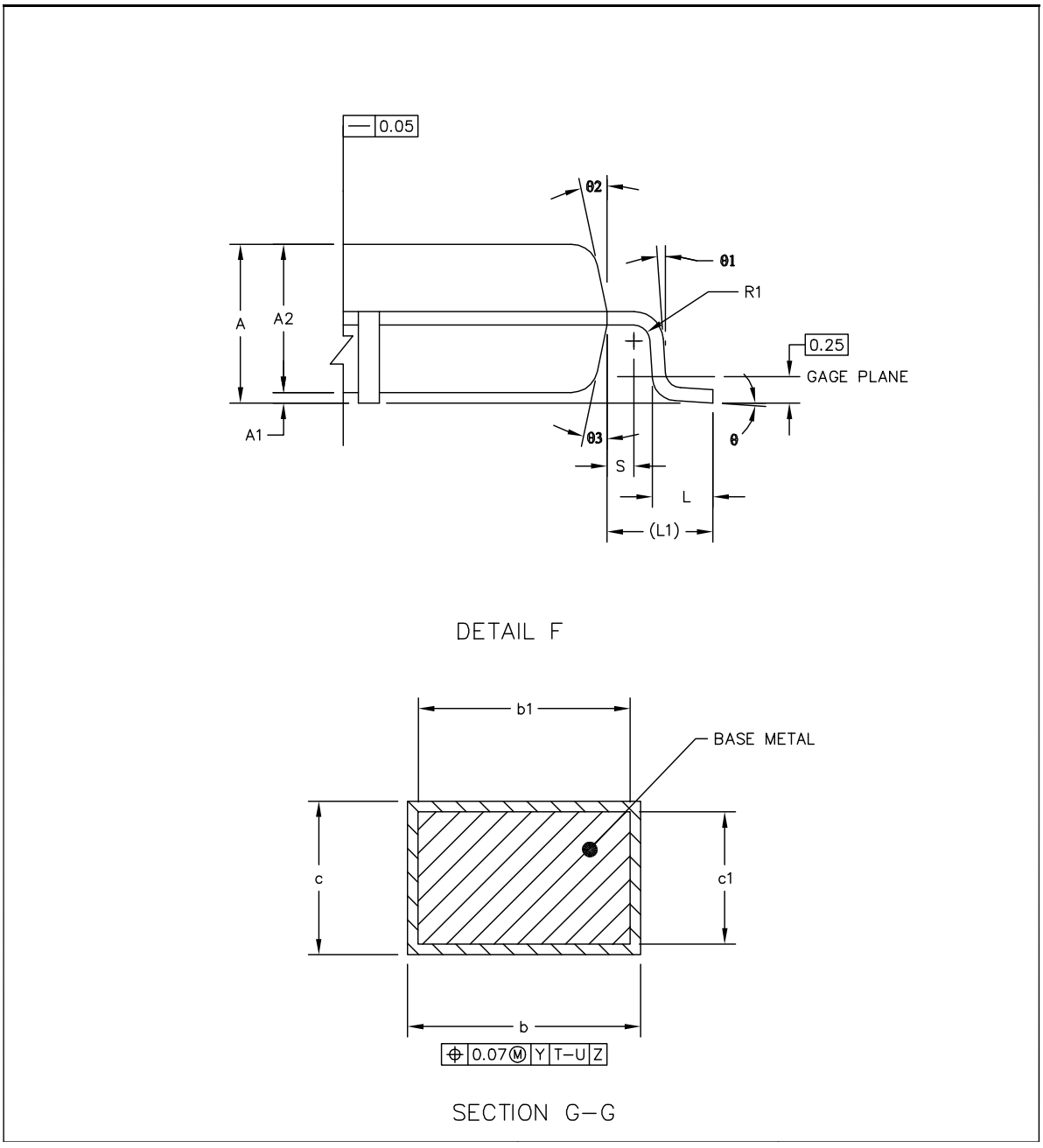


Figure 34. 176 LQFP package mechanical drawing (Part 2 of 3)

Table 51. Revision history (continued)

Revision	Date	Substantive changes
4	24 Aug 2010	Editorial changes and improvements. Updated “Features“ section Table 1: updated footnote concerning 208 MAPBGA In the block diagram: • Added “5ch 12-bit ADC“ block. • Updated Legend. • Added “Interrupt request with wakeup functionality” as an input to the WKPU block. Figure 2: removed alternate functions Figure 3: removed alternate functions Figure 4: removed alternate functions Table 2: added contents concerning the following blocks: CMU, eDMA, ECSM, MC_ME, MC_PCU, NMI, SSCM, SWT and WKPU Added Section 3.2, Pin muxing Section 4, “Electrical characteristics: removed “Caution” note Section 4.2, “NVUSRO register: removed “NVUSRO[WATCHDOG_EN] field description“ section Table 11: V_{IN}: removed min value in “relative to V_{DD}” row Table 12 • $T_{A\ C\text{-}Grade\ Part}$, $T_{J\ C\text{-}Grade\ Part}$, $T_{A\ V\text{-}Grade\ Part}$, $T_{J\ V\text{-}Grade\ Part}$, $T_{A\ M\text{-}Grade\ Part}$, $T_{J\ M\text{-}Grade\ Part}$: added new rows • TV_{DD}: contents merged into one row • V_{DD_BV}: changed min value in “relative to V_{DD}” row Section 4.5, “Thermal characteristics • Section 4.5.1, “External ballast resistor recommendations: added new paragraph about power supply • Table 14: added $R_{\theta JB}$ and $R_{\theta JC}$ rows • Removed “208 MAPBGA thermal characteristics” table Table 15: rewrote parameter description of W_{FI} and W_{NFI} Section 4.6.5, “I/O pad current specification • Removed I_{DYNSEG} information • Updated “I/O supply segments” table Table 22: removed I_{DYNSEG} row Added Table 23 Table 25 • Updated all values • Removed $I_{VREGREF}$ and $I_{VREDLVD12}$ rows • Added the footnote “The duration of the in-rush current depends on the capacitance placed on LV pins. BV decaps must be sized accordingly. Refer to IMREG value for minimum amount of current to be provided in cc.” to the I_{DD_BV} specification. Table 26 • Updated V_{PORH} min/max value • Updated $V_{LVDLVCORL}$ min value Updated Table 27 Table 28 • $T_{dwprogram}$: added initial max value • Inserted T_{eslat} row Table 29: removed the “To be confirmed” footnote In the “Crystal oscillator and resonator connection scheme” figure, removed R_P Table 39 • Removed g_{mSXOSC} row • $I_{SXOSCBIAS}$: added min/typ/max value